

SEMICONDUCTOR
TECHNICAL DATA

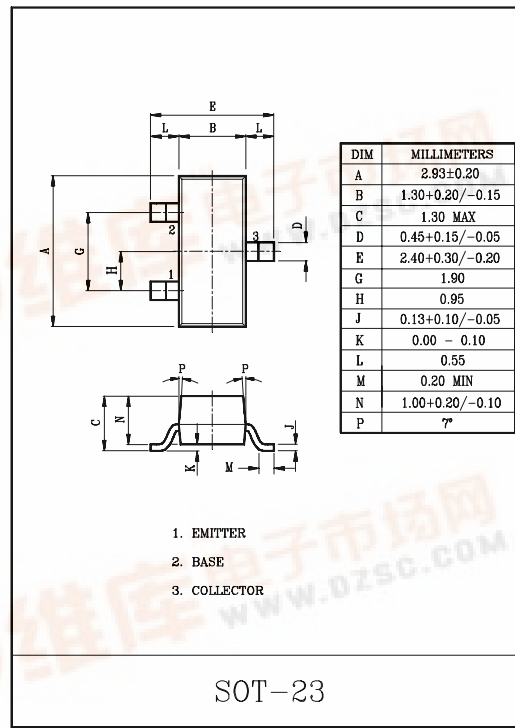
MMBTA92/93

EPITAXIAL PLANAR PNP TRANSISTOR

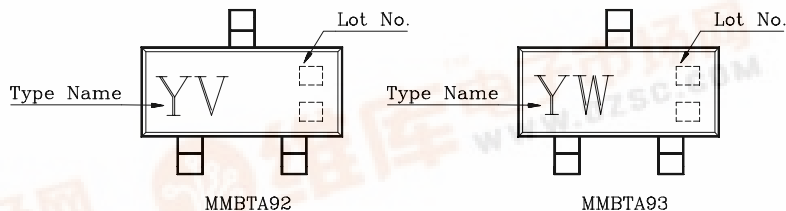
HIGH VOLTAGE APPLICATION.
TELEPHONE APPLICATION.

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage	MMBTA92	V_{CBO}	-300	V
	MMBTA93		-200	
Collector-Emitter Voltage	MMBTA92	V_{CEO}	-300	V
	MMBTA93		-200	
Emitter-Base Voltage		V_{EBO}	-5.0	V
Collector Current		I_C	-500	mA
Emitter Current		I_E	500	mA
Collector Power Dissipation		P_C *	350	mW
Junction Temperature		T_j	150	℃
Storage Temperature		T_{stg}	-55~150	℃

 P_C * : Package mounted on 99.5% alumina $10 \times 8 \times 0.6$ mm.

Marking



ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	MMBTA92	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-300	-	-	V
	MMBTA93			-200	-	-	
Collector-Emitter Breakdown Voltage	MMBTA92	$V_{(BE)CEO}$	$I_C=-1.0mA, I_B=0$	-300	-	-	V
	MMBTA93			-200	-	-	
DC Current Gain		$* h_{FE}$	$I_C=-1.0mA, V_{CE}=-10V$	25	-	-	
			$I_C=-10mA, V_{CE}=-10V$	40	-	-	
			$I_C=-30mA, V_{CE}=-10V$	25	-	-	
Collector-Emitter Saturation Voltage		$* V_{CE(sat)}$	$I_C=-20mA, I_B=-2.0mA$	-	-	-0.5	V
Base-Emitter Saturation Voltage		$* V_{BE(sat)}$	$I_C=-20mA, I_B=-2.0mA$	-	-	-0.9	V
Transition Frequency		f_T	$V_{CE}=-20V, I_C=-10mA, f=100MHz$	50	-	-	MHz
Collector Output Capacitance	MMBTA92	C_{ob}	$V_{CB}=-20V, I_E=0, f=1MHz$	-	-	6.0	pF
	MMBTA93			-	-	8.0	

Pulse Test : Pulse Width ≤ 300μS, Duty Cycle ≤ 2.0%

MMBTA92/93

